

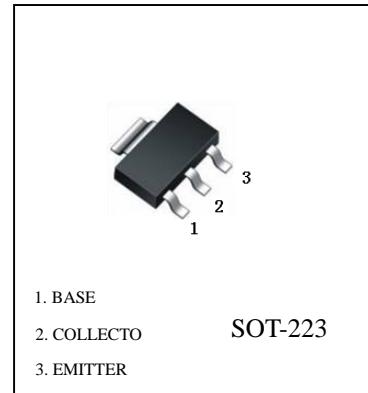
FEATURES

High breakdown voltage

Low collector-emitter saturation voltage

Complementary type: PZTA92(PNP)

PZTA42 (NPN)



MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	300	V
Collector-Emitter Voltage	V _{CEO}	300	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current -Continuous	I _C	500	mA
Collector Power Dissipation	I _C	1	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{Stg}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _C =100μA,I _E =0	300			V
Collector-emitter breakdown voltage	V _{CEO}	I _C =1mA,I _B =0	300			V
Emitter-base breakdown voltage	V _{EBO}	I _E =100μA,I _C =0	6			V
Collector cut-off current	I _{CBO}	V _{CB} =200V,I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =6V,I _C =0			0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =10V,I _C =1mA	25			
	h _{FE(2)}	V _{CE} =10V,I _C =10mA	40			
	h _{FE(3)}	V _{CE} =10V,I _C =30mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =20mA,I _B =2mA			0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =20mA,I _B =2mA			0.9	V
Transition frequency	f _T	V _{CE} =20V,I _C =10mA,f=100MHz	50			MHz
Collector output capacitance	C _{ob}	V _{CB} =20V,I _E =0,f=1MHz			3	pF

PZTA42 Typical Characteristics
